

FRED

Parallel legs

Part number

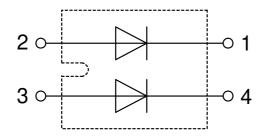
DFE250X600NA





Backside: Isolated





Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper
- internally DCB isolated
- Advanced power cycling

Disclaimer Notice

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DFE250X600NA

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600 V

35 ns

=2x 125 A

 V_{RRM}

t_{rr}



DFE250X600NA

Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{vJ} = 25^{\circ}C$			600	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			600	V
I _R	reverse current, drain current	V_{R} = 600 V	$T_{vJ} = 25^{\circ}C$			3	mA
		V_{R} = 480 V	$T_{vJ} = 125^{\circ}C$			20	mA
V _F	forward voltage drop	I _F = 125 A	$T_{vJ} = 25^{\circ}C$			1.26	V
		I _F = 250 A				1.46	V
		I _F = 125 A	T _{vJ} = 150°C			1.16	V
		I _F = 250 A				1.52	V
I FAV	average forward current	$T_c = 80^{\circ}C$	$T_{vJ} = 150 ^{\circ}C$			125	А
		rectangular d = 0.5					600 V 600 V 3 mA 20 mA .26 V .46 V .16 V .52 V 125 A 0.81 V 2.9 mΩ 0.4 K/W 312 W
V _{F0}	threshold voltage		$T_{vJ} = 150^{\circ}C$			0.81	V
r _F	slope resistance } for power lo	ss calculation only				2.9	mΩ
\mathbf{R}_{thJC}	thermal resistance junction to case	9				0.4	K/W
R _{thCH}	thermal resistance case to heatsir	k			0.10		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			312	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_{R} = 0 V$	$T_{vJ} = 45^{\circ}C$			1.30	kA
C	junction capacitance	$V_{R} = 400 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		107		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25 °C$		27		Α
		$I_{\rm F} = 100 \text{A}; V_{\rm R} = 300 \text{V}$	T _{vJ} = 125 °C		40		Α
t _{rr}	reverse recovery time	I _F = 100 A; V _R = 300 V -di _F /dt = 600 A/μs	$T_{VJ} = 25 ^{\circ}C$		80		ns
		1	$T_{vJ} = 125 ^{\circ}\text{C}$		150		ns

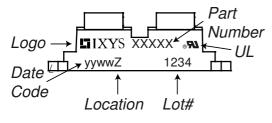
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DFE250X600NA

Package	SOT-227B (minibloc)				F	Ratings	5	
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					150	Α
\mathbf{T}_{v_J}	virtual junction temperature				-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
M _T	terminal torque				1.1		1.5	Nm
d _{Spp/App}	creepage distance on surface	ctriking distance through air	terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}	creepage uistance on surrace i	Sunking distance unough an	terminal to backside	8.6	6.8			mm
V	isolation voltage	t = 1 second			3000			V
		t = 1 minute	50/60 Hz, RMS; liso∟ ≤ 1 mA		2500			V

Product Marking



Part description

D	=	Diode

F = FRED

F = FRED E = fast, low VF 250 = Current Rating [A] X = Parallel legs 600 = Reverse Voltage [V] NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DFE250X600NA	DFE250X600NA	Tube	10	524065

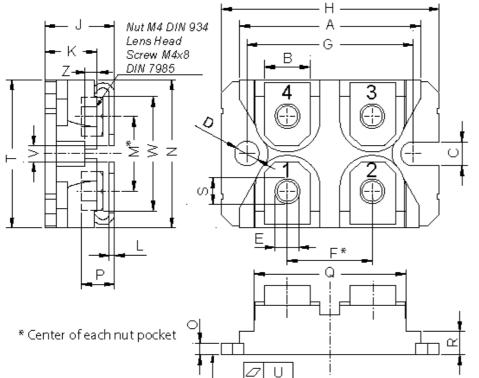
Equivalent Circuits for Simulation			* on die level	$T_{vJ} = 150^{\circ}C$
)[Fast Diode		
V _{0 max}	threshold voltage	0.81		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	1.4		mΩ

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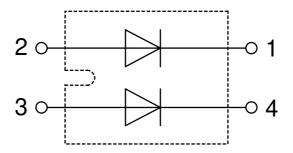
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Outlines SOT-227B (minibloc)



Dim.	Millir	neter	Inches	
Dim.	min	max	min	max
Α	31.50	31.88	1.240	1.255
в	7.80	8.20	0.307	0.323
С	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
Е	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
Н	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
К	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
Μ	12.50	13.10	0.492	0.516
Ν	25.15	25.42	0.990	1.001
0	1.95	2.13	0.077	0.084
Ρ	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
Т	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



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